BATOP optoelectronics

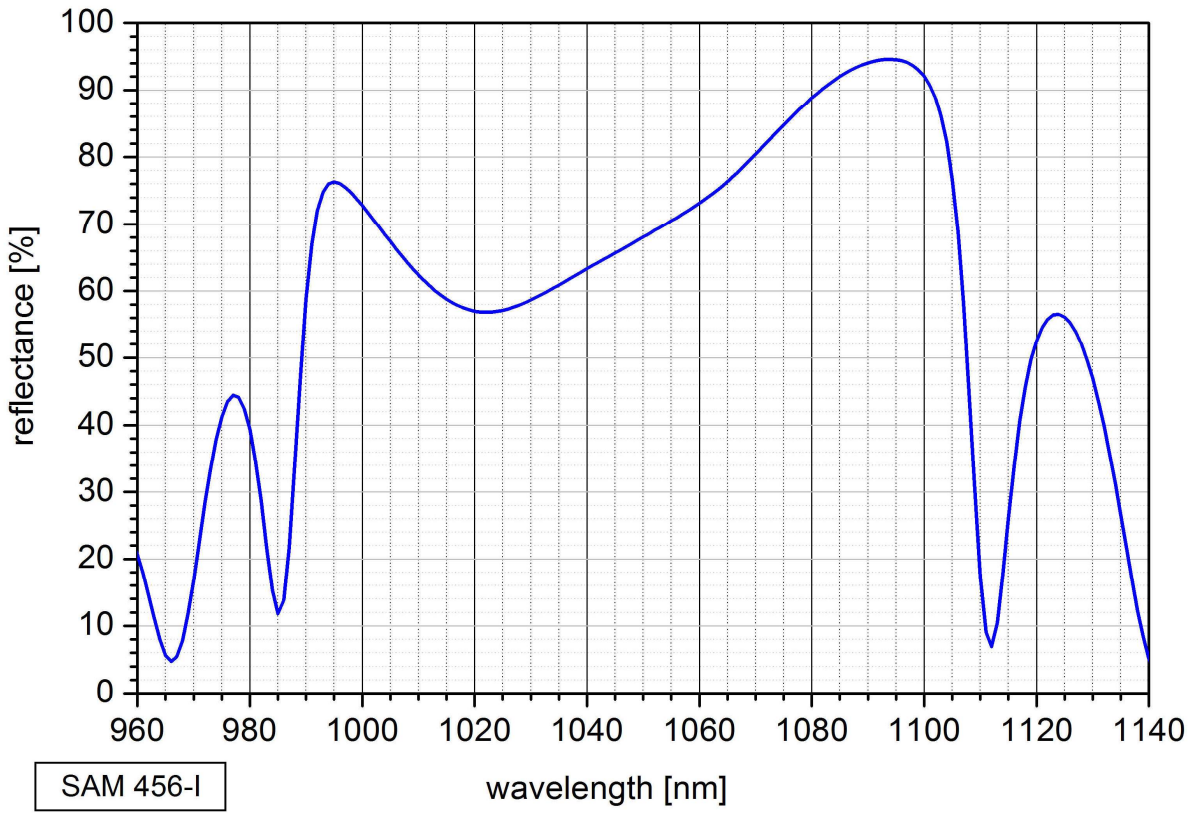
SAM™ Data Sheet SAM-1040-35-9ps-x, λ = 1040 nm

Laser wavelength	λ = 1040 nm
High reflection band	λ = 1000 .. 1100 nm
Absorbance	A_0 = 35 %
Modulation depth	ΔR = 18 %
Non-saturable loss	A_{ns} = 17 %
Saturation fluence	Φ_{sat} = 20 µJ/cm^2
Relaxation time constant	τ ~ 9 ps
Damage threshold	Φ = 1.5 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

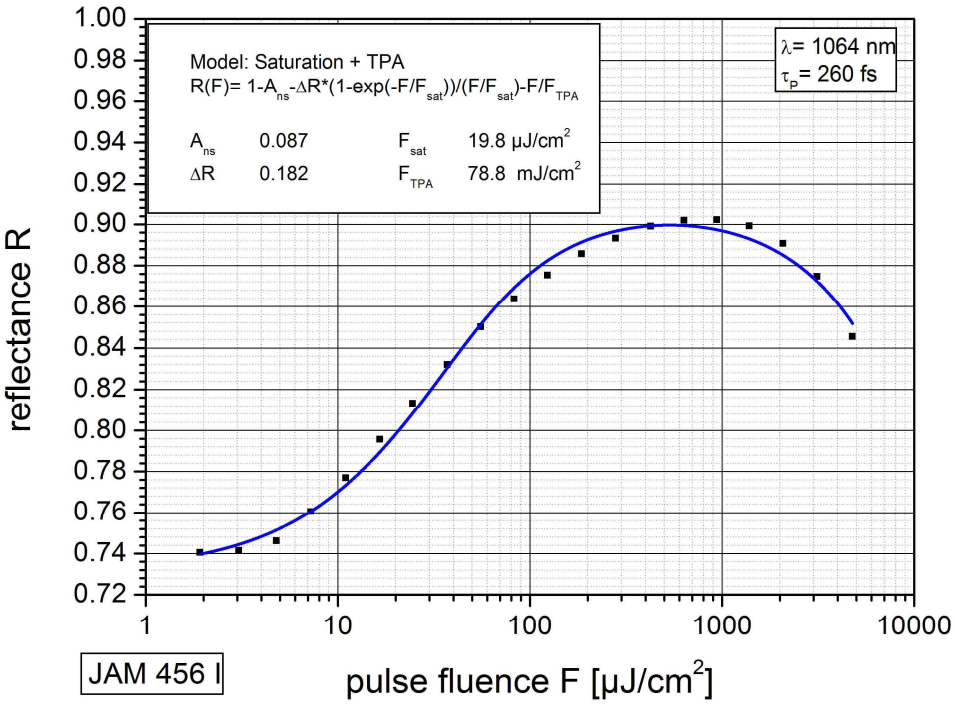
Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance



Saturation measurement



Pump-probe measurement